First-Principles Calculation Analysis on Electronic Structures and Molecular Dynamics of Gadolinium-Doped FAPbI₃ †

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Abstract: First-principle calculation analysis on electronic structures and molecular dynamics was performed to investigate addition of gadolinium ion into the formamidinium lead iodine (FAPbI₃) perovskite crystal for use in application of photovoltaic devices with stability of performance. The band dispersion, density of state, enthalpy, and kinetic energy were expected during the relaxation process. The Gd-doped FAPbI₃ perovskite crystal had effective mass ratio to be 0.02 in narrow band dispersion consisting of 5d and 4f orbital of gadolinium ion, 6p orbital of lead ion, and 5p orbital of iodine ion, supporting the charge transfer and carrier diffusion related to carrier mobility as photovoltaic parameter. The molecular dynamics of the Gd-doped perovskite crystal indicate dynamic stability while suppressing decomposition with separation between nitrogen and hydrogen ions on FA in the crystal. The first-principle calculation expect that the Gd-doped FAPbI₃ perovskite crystal have advantage to apply the perovskite solar cell with stability of the photovoltaic performance.

Keywords: electronic structure; molecular dynamics; gadolinium; perovskite; photovoltaic property

1. Introduction

Metal halide perovskite crystal have been fabricated and characterized for development of industrial materials on photovoltaic devices. Material design and performance prediction of perovskite crystal have been performed for development of perovskite solar cell with optimizing the photovoltaic performance [1–10]. Electronic structure, band distribution with effective mass ratio and band gap were expected by first-principle calculation [11–14]. The photovoltaic properties were based on crystal structure, morphology, and 2/3-dimension interfacial formation [15]. The interface passivation on the crystal grain in the perovskite layer suppressed the carrier trap near defect and pinhole in the perovskite layer, extending carrier life and diffusion related to mobility as the photovoltaic parameters [16–24].

Lanthanide doped perovskite crystal have been used for development of the electronic devices such as wavelength convertor, ultra-visible-near-infrared absorption and luminescence [25–30]. The lanthanide ion at multivalent state caused shuttle redox reaction involving in the redox of lead and halogen ion to regenerate the crystal degradation. For example, slight addition of europium, gadolinium (Gd²⁺), samarium and cerium ions suppressed the decomposition with shuttle redox reaction, reforming the perovskite crystal to achieve a long-term stability of the performance [31,32]. The photovoltaic properties were also related to the band structure with effective mass of hole and electron. Molecular dynamics have been applied for expecting the reaction mechanism, crystal nucleation, formation, decomposition, and energies together with ion diffusion [33–40]. The purpose of this study is to focus on characterization of band structure and molecular dynamics of
formamidinium lead iodide (CH(NH$_2$)$_2$PbI$_3$: FAPbI$_3$) perovskite crystal doped with Gd$^{2+}$ ion for improving the photovoltaic performance and stability.

2. Calculation

The Gd$^{2+}$-doped FAPbI$_3$ perovskite crystal was assembled with supercells (2 × 2 × 2) based on the FAPbI$_3$ crystals as a cubic crystal phase (cubic $Pm\bar{3}m$) with experimental lattice constants (FAPbI$_3$: $a = 6.3621$ Å) [32,33,41–43]. Partial substitution of Gd$^{2+}$ ions for Pb$^{2+}$ cation ion was introduced at center of cubic structure. The ab initio quantum calculations were performed by using the Vanderbilt ultrasoft pseudo-potentials, scalar relativistic generalized gradient approximations, and density functional theory (DFT) (Quantum Espresso, v.5.2.1, Quantum Espresso Foundation, UK). The band structures, effective mass ratio of electron and hole to free electron ($m_e^*/m_e$ and $m_h^*/m_e$), band gap ($E_g$) and density of state (DOS) near valence (VB) and conduction band (CB) states were expected.

Car–Parrinello molecular dynamics (CPMD) simulations have been performed with Quantum Espresso. Plane-wave basis set cutoffs for the smooth part of the wave functions and the augmented density were 80 and 3 20 Ry, respectively. The CPMD simulations were performed during an integration time step of 150 for a total simulation time of 0.018 psec. The enthalpy, kinetic energy and molecular dynamics were followed during the relaxation process near 300 K.

3. Results and Discussion

The first-principle calculation analysis was performed to investigate addition of Gd$^{2+}$ ion into the perovskite crystal on the electron density distribution, band dispersion and DOS. The electron density distribution of the Gd-doped FAPbI$_3$ perovskite crystal is shown in Figure 1a. The partially occupied 6s, 6p, and 5d orbital and fully occupied 4f orbital of Gd$^{2+}$ ion, and partially occupied 5s and 5p orbital of iodine ion as ligand were distributed and overlapped each other, sharing the electron between the Gd$^{2+}$ ion and iodine ion to form the coordination bond. Ligand-metal charge transfer between the Gd$^{2+}$ ion and iodine ion are caused, supporting the carrier generation and diffusion related to carrier mobility as photovoltaic parameter. The band dispersion and DOS are shown in Figure 1b,c. The 5p orbital of iodine ion were widely distributed in the range from $-3$ eV to $-2$ eV near VB state, and 6p orbital of lead ion, 5d orbitals and 4f orbital of Gd$^{2+}$ ion were also distributed in the range from 0 eV to 1.5 eV near CB state. Effective mass ratio ($m_e^*/m_e$ and $m_h^*/m_e$) were calculated to be 0.02 and 0.02 from the band dispersion near VB and CB states. The direct band gap ($E_g$) at the $\Gamma$ position as $k$-vector was obtained to be about 1.52 eV, as semi-conductive characteristics. The Gd$^{2+}$-doped FAPbI$_3$ crystal had the narrow band dispersion with the same order of effective mass ratio, as similar to those of the FAPbI$_3$ crystal. The photovoltaic performance related to short circuit current density based on the carrier mobility will be maintained. The formation energies of the Gd$^{2+}$-doped crystal and FAPbI$_3$ crystal were obtained to be $-4662$ eV cell$^{-1}$ and $-3745$ eV cell$^{-1}$, which indicates stability of the Gd$^{2+}$-doped FAPbI$_3$ crystal.

Enthalpy and kinetic energy of the Gd$^{2+}$-doped FAPbI$_3$ and FAPbI$_3$ crystal was calculated for expecting the crystal formation, dynamic stability and kinetics of reaction mechanism such as decomposition. The dynamic behaviors regarding the enthalpy and kinetic energy during the relaxation time are shown in Figure 2a. In both cases, similar behavior of the kinetic energies was qualitatively demonstrated. Addition of Gd$^{2+}$ ion into the perovskite crystal caused a gradual decreasing behavior of the enthalpy during the relaxation time. The energy fluctuations were based on the crystal stability with slight distortion of the coordination structure. The kinetic energies behavior of the Gd$^{2+}$-doped FAPbI$_3$ crystal as similar to those of the FAPbI$_3$ crystal indicate dynamic stability as reaching equilibrium at the final stage. The kinetic energy behavior was derived from the dynamic stability related with degree of distortion of the coordination structure with variation in the position of FA, Gd$^{2+}$ ion and iodine ion as ligand. The structural distortions and molecular
dynamics would be suppressed by the addition of Gd$^{2+}$ ion. For making clear the dynamic behavior, the structural distortion of FA in the Gd$^{2+}$-doped FAPbI$_3$ crystal and FAPbI$_3$ crystal was characterized by molecular dynamics calculation.

Distance of nitrogen (N) and hydrogen (H) atom in FA of the Gd$^{2+}$-doped FAPbI$_3$ crystal and FAPbI$_3$ crystal were considered as shown in Figure 2b. In the case of the FAPbI$_3$ crystal, the distance of N-H band in FA was drastically increased, as separation between N-H bands in FA at time of 0.0169 psec. The atomic position of Pb$^{2+}$ ion located in the center of the FAPbI$_3$ crystal was shifted, shrinking the coordination structure in the perovskite crystal as the decomposition. The distortion of crystal structures was induced with a reduction in the thermal energy. In the case of the Gd$^{2+}$-doped FAPbI$_3$ crystal, the distance between N and H atom in FA was slightly decreased, as dynamic stability of FA. The atomic position of Pb$^{2+}$ ion located in the center of the coordination structure was maintained at final stage. Addition of Gd$^{2+}$ ion into the crystal maintained stabilization, while suppressing the crystal distortions and the separation between N-H bands in FA as decomposition. The calculation prediction indicates that the Gd$^{2+}$-doped FAPbI$_3$ perovskite crystal have advantage to apply the photovoltaic devices with the stability of performance.

Figure 1. (a) Electron density distribution (b) band dispersion and (c) DOS of the Gd-doped FAPbI$_3$ perovskite crystal.
4. Conclusions

The first-principles calculation expected the band dispersion, DOS, electron density distribution, enthalpy, kinetic energy, and molecular dynamics of the Gd²⁺-doped FAPbI₃ crystal, as compared with those of the FAPbI₃ crystal. The Gd²⁺-doped FAPbI₃ crystal had the effective mass ratio to be 0.02 in the narrow band dispersion consisting of 5d orbital of Gd²⁺ ion, 6p orbital of Pb²⁺ ion, and 5p orbital of I⁻ ion as ligand, causing the metal-ligand charge transfer, carrier generation and diffusion related to the mobility as the photovoltaic parameter. The molecular dynamics indicates more dynamic stability and crystal formation for the Gd²⁺-doped FAPbI₃ crystal rather than the FAPbI₃ crystal while suppressing the decomposition with the separation of N-H band on FA. The first-principles calculation analysis expects that the Gd²⁺-FAPbI₃ doped crystal have advantage to apply the perovskite solar cell with stability of the photovoltaic performance.

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